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Single Inverter with Schmitt-Trigger Input

MC74HC1G14

The MC74HC1G14 is a high speed CMOS inverter with Schmitt-Trigger input fabricated with silicon gate CMOS technology.

The internal circuit is composed of multiple stages, including a buffer output which provides high noise immunity and stable output.

The MC74HC1G14 output drive current is 1/2 compared to MC74HC series.

Features

- High Speed: $t_{PD} = 7 \text{ ns} (Typ)$ at $V_{CC} = 5 \text{ V}$
- Low Power Dissipation: $I_{CC} = 1 \mu A$ (Max) at $T_A = 25^{\circ}C$
- High Noise Immunity
- Balanced Propagation Delays (t_{pLH} = t_{pHL})
- Symmetrical Output Impedance $(I_{OH} = I_{OL} = 2 \text{ mA})$
- Chip Complexity: < 100 FETs
- -Q Suffix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

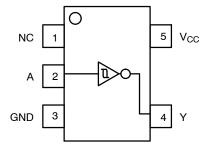


Figure 1. Pinout

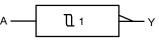
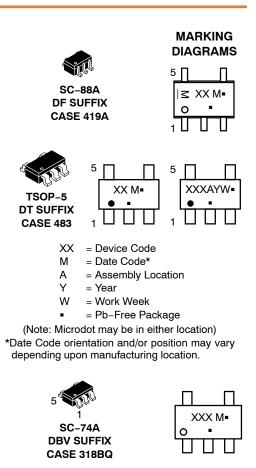


Figure 2. Logic Symbol

PIN ASSIGNMENT					
1	N/C				
2	A				
3	GND				
4	Y				
5	V _{CC}				



XXX= Specific Device CodeM= Date Code•= Pb-Free Package

(Note: Microdot may be in either location)

FUNCTION TABLE

Input	Output
А	Y
L	н
Н	L

ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 5 of this data sheet.

MC74HC1G14

MAXIMUM RATINGS

Symbol	Parameter		Value	Unit
V _{CC}	DC Supply Voltage		–0.5 to +6.5	V
V _{IN}	DC Input Voltage		–0.5 to V _{CC} +0.5	V
V _{OUT}	DC Output Voltage		–0.5 to V _{CC} +0.5	V
I _{IK}	DC Input Diode Current		±20	mA
I _{ОК}	DC Output Diode Current		±20	mA
I _{OUT}	DC Output Source/Sink Current		±12.5	mA
I _{CC} or I _{GND}	DC Supply Current per Supply Pin or Ground Pin	±25	mA	
T _{STG}	Storage Temperature Range	-65 to +150	°C	
ΤL	Lead Temperature, 1 mm from Case for 10 Seconds		260	°C
TJ	Junction Temperature Under Bias		+150	°C
θ_{JA}	Thermal Resistance (Note 1)	SC-88A SC-74A	377 320	°C/W
PD	Power Dissipation in Still Air	SC-88A SC-74A	332 390	mW
MSL	Moisture Sensitivity		Level 1	
F _R	Flammability Rating	Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in	
V _{ESD}	ESD Withstand Voltage (Note 2)	Human Body Model Charged Device Model	2000 1000	V
I _{LATCHUP}	Latchup Performance (Note 3)		±100	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected. 1. Measured with minimum pad spacing on an FR4 board, using 10 mm-by-1 inch, 20 ounce copper trace with no air flow per JESD51-7.

2. HBM tested to ANSI/ESDA/JEDEC JS-001-2017. CDM tested to JESD22-C101-F. JEDEC recommends that ESD qualification to EIA/JESD22-A115A (Machine Model) be discontinued per JEDEC/JEP172A.

3. Tested to EIA/JESD78 Class II.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{CC}	DC Supply Voltage	2.0	6.0	V
V _{IN}	DC Input Voltage	0.0	V _{CC}	V
V _{OUT}	DC Output Voltage	0.0	V _{CC}	V
T _A	Operating Temperature Range	-55	+125	°C
t _r , t _f	Input Rise and Fall Time $\begin{array}{c} V_{CC} = 2.0 \ V \\ V_{CC} = 2.3 \ V \ to \ 2.7 \ V \\ V_{CC} = 3.0 \ V \ to \ 3.6 \ V \\ V_{CC} = 4.5 \ V \ to \ 6.0 \ V \end{array}$	- - - -	No Limit No Limit No Limit No Limit	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

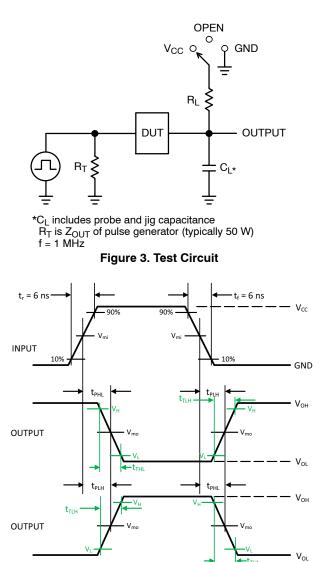
		Test	v _{cc}	Т	A = 25°	C	-40°C ≤ 1	Γ _A ≤ 85°C	-55°C ≤ T	<mark>A</mark> ≤ 125°C	
Symbol	Parameter	Conditions	(V)	Min	Тур	Max	Min	Max	Min	Max	Unit
V _{T+}	Positive Threshold		3.0	-	2.0	2.2	-	2.2	-	2.2	V
	Voltage		4.5	-	3.0	3.15	-	3.15	-	3.15	
			5.5	-	3.6	3.85	-	3.85	-	3.85	
V_{T-}	Negative Threshold		3.0	0.9	1.5	-	0.9	-	0.9	-	V
	Voltage		4.5	1.35	2.3	-	1.35	-	1.35	-	
			5.5	1.65	2.9	-	1.65	-	1.65	-	
V _H	Hysteresis Voltage		3.0 4.5 5.5	0.30 0.40 0.50	0.57 0.67 0.74	1.20 1.40 1.60	0.30 0.40 0.50	1.20 1.40 1.60	0.30 0.40 0.50	1.20 1.40 1.60	V
V _{OH}	High-Level Output Voltage		2.0 3.0 4.5 6.0	1.9 2.9 4.4 5.9	2.0 3.0 4.5 6.0	- - -	1.9 2.9 4.4 5.9	- - -	1.9 2.9 4.4 5.9		V
		$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -2 \text{ mA}$ $I_{OH} = -2.6 \text{ mA}$	4.5 6.0	4.18 5.68	4.31 5.80		4.13 5.63		4.08 5.58		
V _{OL}	Low-Level Output Voltage		2.0 3.0 4.5 6.0	- - -	0.0 0.0 0.0 0.0	0.1 0.1 0.1 0.1		0.1 0.1 0.1 0.1		0.1 0.1 0.1 0.1	V
		$\begin{array}{l} V_{IN} = V_{IH} \text{ or } V_{IL} \\ I_{OL} = 2 \text{ mA} \\ I_{OL} = 2.6 \text{ mA} \end{array}$	4.5 6.0		0.17 0.18	0.26 0.26		0.33 0.33		0.40 0.40	
I _{IN}	Input Leakage Current	V _{IN} = 6.0 V or GND	6.0	-	-	±0.1	-	±1.0	-	±1.0	μΑ
I _{CC}	Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND	6.0	-	-	1.0	-	10	-	40	μΑ

AC ELECTRICAL CHARACTERISTICS

			Ţ	T _A = 25°C		$-40^\circ C \le T_A \le 85^\circ C$		$-55^\circ C \leq T_A \leq 125^\circ C$		
Symbol	Parameter	Test Conditions	Min	Тур	Max	Min	Max	Min	Max	Unit
t _{PLH} ,	Propagation Delay,	$V_{CC} = 5.0 \text{ V}$ $C_{L} = 15 \text{ pF}$	-	3.5	15	-	20	-	25	ns
^t PHL	Input A or B to Y	$ \begin{array}{l} V_{CC} = 2.0 \ V \ C_L = 50 \ pF \\ V_{CC} = 3.0 \ V \\ V_{CC} = 4.5 \ V \\ V_{CC} = 6.0 \ V \end{array} $		19 10.5 7.5 6.5	100 27 20 17		125 35 25 21		155 90 35 26	
t _{TLH} ,	Output Transition	$V_{CC} = 5.0 \text{ V}$ C _L = 15 pF	-	3	10	-	15	-	20	ns
t _{THL}	Time	$ \begin{array}{l} V_{CC} = 2.0 \ V \ \ C_L = 50 \ pF \\ V_{CC} = 3.0 \ V \\ V_{CC} = 4.5 \ V \\ V_{CC} = 6.0 \ V \end{array} $		25 16 11 9	125 35 25 21		155 45 31 26		200 60 38 32	
C _{IN}	Input Capacitance		-	5	10	-	10	-	10	pF
				Typical @ 25°C, V _{CC} = 5.0 V						

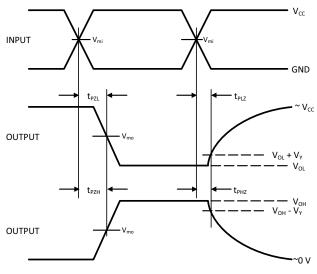
 C_{PD} Power Dissipation Capacitance (Note 4)10pF4. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.
Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC}$. C_{PD} is used to determine the no-load dynamic power consumption; $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$.

MC74HC1G14



Test	Switch Position	C _L , pF	R_L, Ω
t_{PLH} / t_{PHL}	Open		Х
t _{TLH} / t _{THL} (Note 5)	Open	See AC Characteristics Table	х
t _{PLZ} / t _{PZL}	V _{CC}	Table	1 k
t_{PHZ} / t_{PZH}	GND		1 k

X - Don't Care





		V _{mo} , V				
v_{cc}, v	V _{mi} , V	t _{PLH} , t _{PHL}	$t_{\text{PZL}}, t_{\text{PLZ}}, t_{\text{PZH}}, t_{\text{PHZ}}$	V _L , V	V _H , V	V _Y , V
3.0 to 3.6	V _{CC} /2	V _{CC} /2	V _{CC} /2	V _{OL} + 0.1 (V _{OH} – V _{OL})	V _{OL} + 0.9 (V _{OH} – V _{OL})	0.3
4.5 to 5.5	V _{CC} /2	V _{CC} /2	V _{CC} /2	V _{OL} + 0.1 (V _{OH} – V _{OL})	V _{OL} + 0.9 (V _{OH} – V _{OL})	0.3

5. t_{TLH} and t_{THL} are measured from 10% to 90% of (V_{OH} - V_{OL}), and 90% to 10% of (V_{OH} - V_{OL}), respectively.

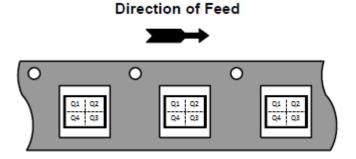
ORDERING INFORMATION

Device	Packages	Specific Device Code	Pin 1 Orientation (See below)	Shipping [†]
MC74HC1G14DFT1G	SC-88A	HA	Q2	3000 / Tape & Reel
MC74HC1G14DFT1G-Q* (Please contact onsemi)	SC-88A	HA	Q2	3000 / Tape & Reel
MC74HC1G14DFT2G	SC-88A	HA	Q4	3000 / Tape & Reel
MC74HC1G14DFT2G-Q* (Please contact onsemi)	SC-88A	HA	Q4	3000 / Tape & Reel
MC74HC1G14DTT1G-Q* (Please contact onsemi)	TSOP-5	HA	Q4	3000 / Tape & Reel
MC74HC1G14DBVT1G	SC-74A	HA	Q4	3000 / Tape & Reel

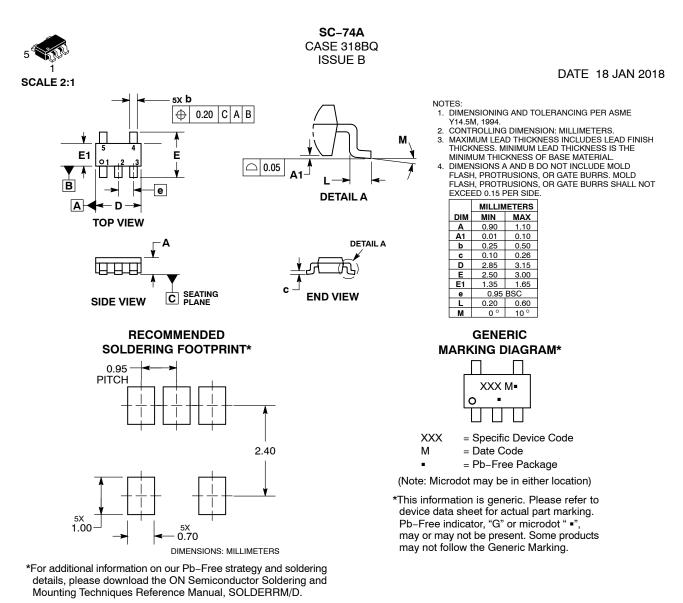
+For complete information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. *-Q Suffix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP

Capable.

Pin 1 Orientation in Tape and Reel







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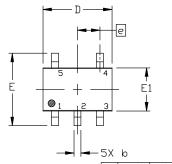
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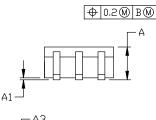
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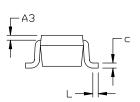
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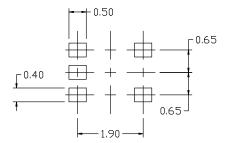
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DATE 11 APR 2023









RECOMMENDED MOUNTING FOOTPRINT

For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

DIM	MILLIMETERS					
INIT	MIN,	NDM.	MAX.			
A	0.80	0.95	1.10			
A1			0.10			
A3	0.20 REF					
b	0.10	0.20	0,30			
С	0.10		0,25			
D	1.80	2.00	5'50			
E	2.00	2.10	5,20			
E1	1.15	1.25	1.35			
e		0.65 BSI	С			
L	0.10	0.15	0.30			

DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH,

PROTRUSIONS, OR GATE BURRS.MOLD FLASH, PROTRUSIONS,

OR GATE BURRS SHALL NOT EXCEED 0.1016MM PER SIDE.

CONTROLLING DIMENSION: MILLIMETERS 419A-01 DBSDLETE, NEW STANDARD 419A-02

GENERIC MARKING





*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

(Note: Microdot may be in either location)

STYLE 1: PIN 1. BASE 2. EMITTER 3. BASE 4. COLLECTOR 5. COLLECTOR	STYLE 2: PIN 1. ANODE 2. EMITTER 3. BASE 4. COLLECTOR 5. CATHODE	STYLE 3: PIN 1. ANODE 1 2. N/C 3. ANODE 2 4. CATHODE 2 5. CATHODE 1	STYLE 4: PIN 1. SOURCE 1 2. DRAIN 1/2 3. SOURCE 1 4. GATE 1 5. GATE 2	STYLE 5: PIN 1. CATHODE 2. COMMON ANOD 3. CATHODE 2 4. CATHODE 3 5. CATHODE 4	ΡE
STYLE 6: PIN 1. EMITTER 2 2. BASE 2 3. EMITTER 1 4. COLLECTOR 5. COLLECTOR 2/BASE	STYLE 7: PIN 1. BASE 2. EMITTER 3. BASE 4. COLLECTOR 1 5. COLLECTOR	STYLE 8: PIN 1. CATHODE 2. COLLECTOR 3. N/C 4. BASE 5. EMITTER	STYLE 9: PIN 1. ANODE 2. CATHODE 3. ANODE 4. ANODE 5. ANODE	Note: Please refer to style callout. If style to out in the datasheet r datasheet pinout or p	ype is not called refer to the device
DOCUMENT NUMBER:	98ASB42984B			ot when accessed directly from when stamped "CONTROLLED (
DESCRIPTION:	SC-88A (SC-70-	5/SOT-353)			PAGE 1 OF 1

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XXX = Specific Device Code

M = Date Code = Pb-Free Package

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Europe, Middle East and Africa Technical Support: Phone: 00421 33 790 2910 For additional information, please contact your local Sales Representative 单击下面可查看定价,库存,交付和生命周期等信息

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